

## 1500V,9A N-Channel MOSFET

### DESCRIPTION

- High speed switch
- Extremely low threshold voltage
- Ultra High Voltage
- Low On-Resistance

### FEATURES

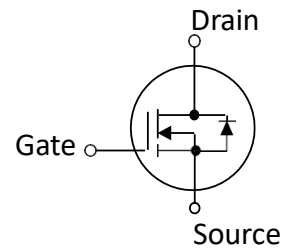
- $BV_{DSS} \geq 1500V$
- $I_D = 9A$
- $R_{DS(ON)} \leq 4.2m\Omega @ V_{GS}=10V$

$BV_{DSS}$	$R_{DS(ON),typ.}$	$I_D$
1500V	4.2m $\Omega$	9A



TO-247

Package



### Application

- Portable appliances
- Hard switched and high frequency circuits
- Power management
- Uninterruptible power supply

### Ordering Information

Part Number	Package
SK09N150-T7	TO-247

### Absolute Maximum Ratings (T<sub>c</sub>=25°C Unless Otherwise Noted)

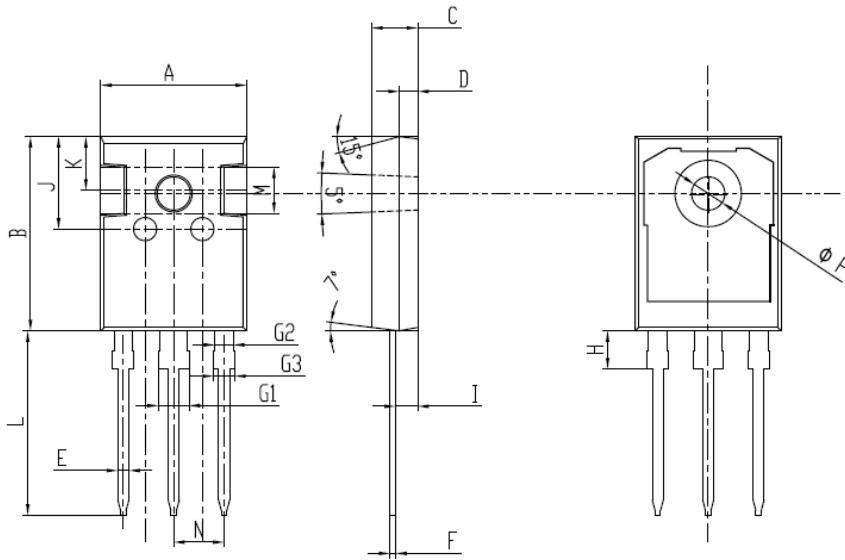
Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	V <sub>DS</sub>	1500	V
Gate-Source Voltage	V <sub>GS</sub>	±30	V
Drain Current - Continues	I <sub>D</sub>	9	A

- Electrical Characteristics ( Ta = 25 °C Unless Otherwise Noted )

Parameter	Description	Min.	Typ.	Max.	Test Conditions	Unit
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	1500	--	--	$V_{GS} = 0V, I_D = 250\mu A$	V
$V_{GSS}$	Gate-to-Source Voltage	--	--	$\pm 30$	NA	V
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	--	--	4.2	$V_{GS} = 10V, I_D = 5.4A$	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	2.5	--	4.5	$V_{DS} = V_{GS}, I_D = 250\mu A$	V
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	1.0	$V_{DS} = 1500V, V_{GS} = 0V, T_J = 25^\circ C$	$\mu A$
$I_{GSS}$	Gate-to-Source Leakage Current	--	--	$\pm 100$	$V_{GS} = \pm 30V$	nA
$V_{SD}$	Body Diode Voltage	--	--	1.5	$V_{GS} = 0V, I_{SD} = 9.0A$	V
$T_j$	Operating Junction and	-55°C to 150 Max.				°C
$T_{STG}$	Storage Temperature Range					

## PACKAGE OUTLINE

TO-247



	(mm)	
	MIN	MAX
A	15.70	15.90
B	20.90	21.10
C	4.90	5.10
D	1.90	2.10
E	1.10	1.30
F	0.45	0.75
G1	3.00	3.20
G2	1.85	2.15
G3	2.00	2.20
H	4.00	4.30
I	2.30	2.50
J	9.90	10.10
K	5.70	5.90
L	19.80	20.20
M	4.85	5.15
N	5.286	5.586
$\phi P$	3.40	3.60

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)